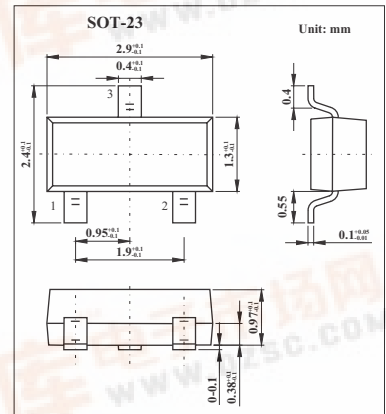


SMD Type Diodes

Silicon Schottky Barrier Diode HSM88ASR

■ Features

- Proof against high voltage.
- MPAK package is suitable for high density surface mounting and high speed assembly.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Reverse voltage	VR	10	V
Average rectified current	Io	15	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55 to +125	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	VF	IF = 1 mA	350		420	mV
		IF = 10 mA	500		580	
Reverse current	IR	VR = 2 V			0.2	μ A
		VR = 10 V			10	
Capacitance	C	VR = 0 V, f = 1 MHz			0.85	pF
Capacitance deviation	ΔC	VR = 0 V, f = 1 MHz			0.10	pF
Forward voltage deviation	ΔVF	IF = 10 mA			10	mV
ESD-Capability (Note 1)		C=200pF, Both forward and reverse direction 1 pulse.	30			V

Note

1. Failure criterion ; IR ≥ 400nA at VR = 2 V

■ Marking

Marking	C3
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